

PMK30EP

P-channel TrenchMOS extremely low level FET

Rev. 04 — 25 October 2010

Product data sheet

1. Product profile

1.1 General description

Extremely low level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

 Low conduction losses due to low on-state resistance

1.3 Applications

Battery management

Load switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	-	-30	V
I _D	drain current	$T_{sp} = 25 ^{\circ}\text{C}; V_{GS} = -10 \text{V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	-14. 9	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	6.9	W
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -9.2 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	16	19	mΩ
Dynamic cl	naracteristics					
Q_{GD}	gate-drain charge	V_{GS} = -10 V; I_D = -9.2 A; V_{DS} = -15 V; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	7	-	nC



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	8 <u> </u>	D
3	S	source		
4	G	gate		G L L
5	D	drain	1	
6	D	drain	SOT96-1 (SO8)	S 001aaa025
7	D	drain		
8	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMK30EP	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Limiting values

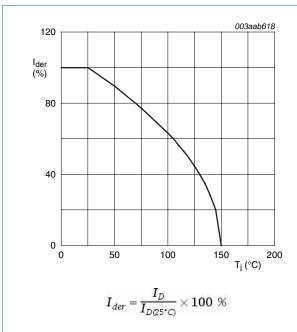
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

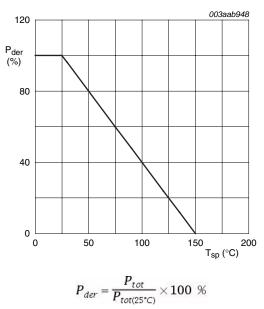
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	-30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 150 °C; R_{GS} = 20 $k\Omega$	-	-30	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$T_{sp} = 25 \text{ °C}$; $V_{GS} = -10 \text{ V}$; see Figure 1; see Figure 3	-	-14.9	Α
		$T_{sp} = 100 ^{\circ}\text{C}; V_{GS} = -10 \text{V}; \text{see } \frac{\text{Figure 1}}{}$	-	-7.5	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3	-	-28.8	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	6.9	W
T _{stg}	storage temperature		-55	150	°C
Tj	junction temperature		-55	150	°C
Source-drai	in diode				
Is	source current	$T_{sp} = 25 ^{\circ}C$	-	-5.8	Α
I _{SM}	peak source current	$T_{sp} = 25 \text{ °C}$; pulsed; $t_p \le 10 \mu\text{s}$	-	-23	Α

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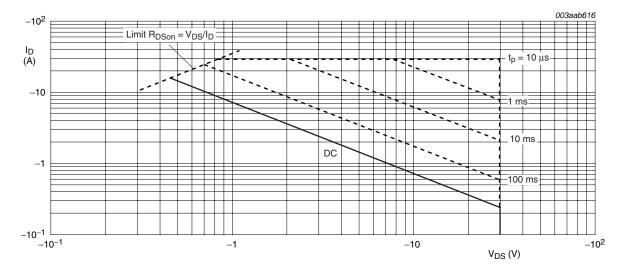
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Normalized continuous drain current as a function of solder point temperature







 $T_{sp} = 25 \, ^{\circ}C; I_{DM}$ is single pulse

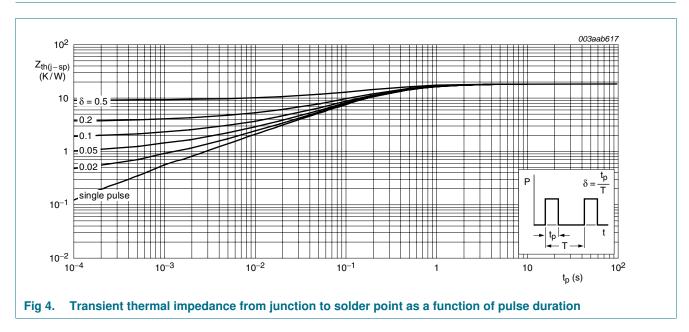
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 4	-	-	18	K/W



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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
	voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	-27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 7</u> ; see <u>Figure 8</u>	-1	-	-3	V
		$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 150 \text{ °C}$; see Figure 7; see Figure 8	-0.7	-	-	V
		$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 7; see Figure 8	-	-	-3.3	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 70 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
D0011	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -9.2 \text{ A}; T_j = 25 \text{ °C};$ see Figure 9	-	16	19	mΩ
		$V_{GS} = -10 \text{ V}; I_D = -9.2 \text{ A}; T_j = 150 \text{ °C};$ see Figure 9	-	25	31	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -7.3 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 9	-	24	30	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = -9.2 \text{ A}$; $V_{DS} = -15 \text{ V}$; $V_{GS} = -10 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	50	-	nC
Q_{GS}	gate-source charge	$I_D = -9.2 \text{ A}$; $V_{DS} = -15 \text{ V}$; $V_{GS} = -10 \text{ V}$; see Figure 11; see Figure 12	-	7	-	nC
Q_{GD}	gate-drain charge	$I_D = -9.2 \text{ A}$; $V_{DS} = -15 \text{ V}$; $V_{GS} = -10 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	7	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = -9.2 \text{ A}$; $V_{DS} = -15 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; see Figure 11; see Figure 12	-	-2.5	-	V
C _{iss}	input capacitance	$V_{DS} = -25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2240	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 13</u>	-	325	-	рF
C_{rss}	reverse transfer capacitance		-	220	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -15 \text{ V}; R_L = 6 \Omega; V_{GS} = -10 \text{ V};$	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	8	-	ns
t _{d(off)}	turn-off delay time		-	56	-	ns
t _f	fall time		-	21	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -3.45 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 14	-	-0.8	-1.2	V

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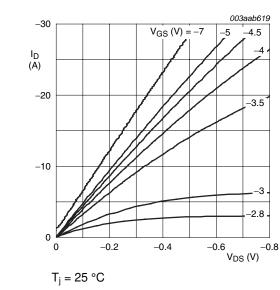
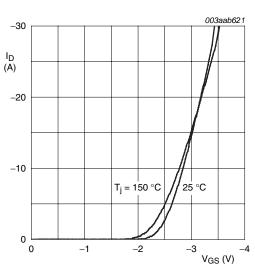


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

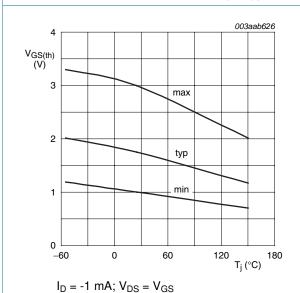
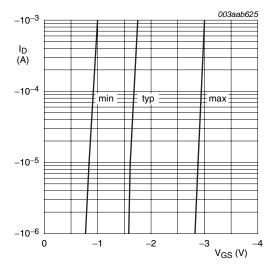


Fig 7. Gate-source threshold voltage as a function of junction temperature



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

Fig 8. Sub-threshold drain current as a function of gate-source voltage

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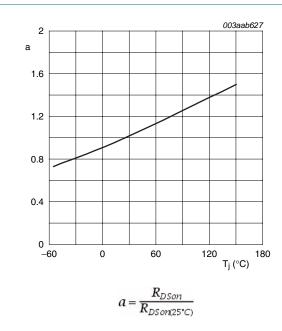


Fig 9. Normalized drain-source on-state resistance factor as a function of junction temperature

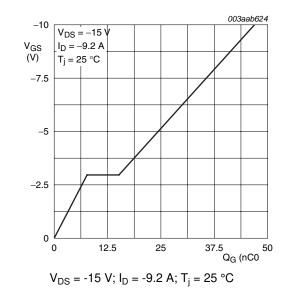


Fig 11. Gate-source voltage as a function of gate charge; typical values

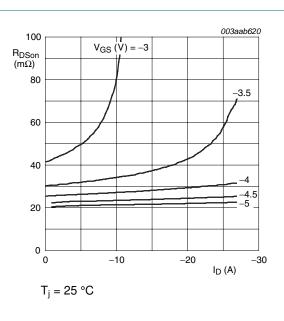


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

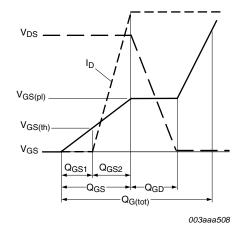


Fig 12. Gate charge waveform definitions

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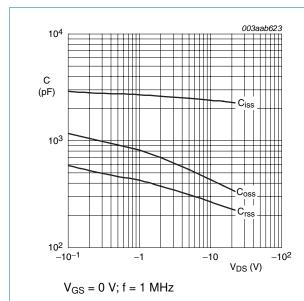


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

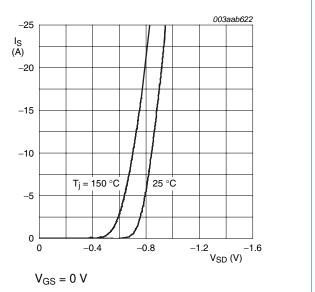


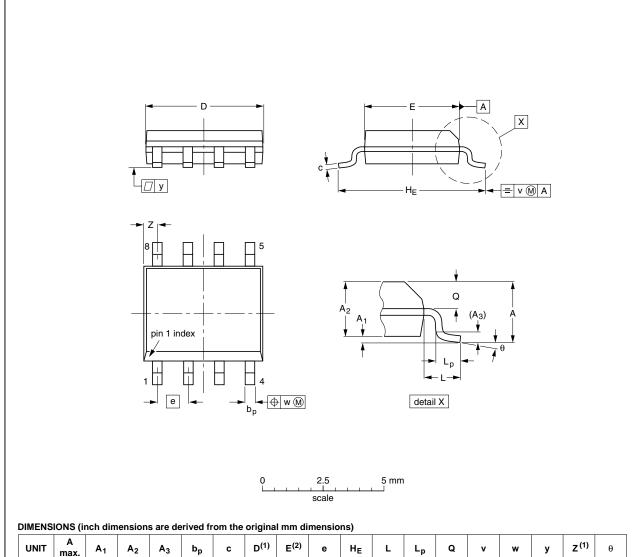
Fig 14. Source current as a function of source-drain voltage; typical values

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7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	σ	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012				99-12-27 03-02-18

Fig 15. Package outline SOT96-1 (SO8)

PMK30EF

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMK30EP v.4	20101025	Product data sheet	-	PMK30EP v.3
Modifications:	 Various chang 	ges to content.		
PMK30EP v.3	20100429	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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